

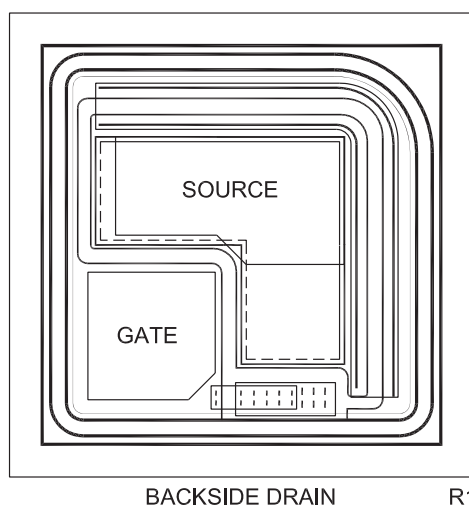
PROCESS CP761R
Small Signal MOSFET
P-Channel Enhancement-Mode MOSFET Chip



PROCESS DETAILS

Die Size	14.2 x 14.2 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.94 x 3.94 MILS
Source Bonding Pad Area	3.94 x 7.08 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER

123,000

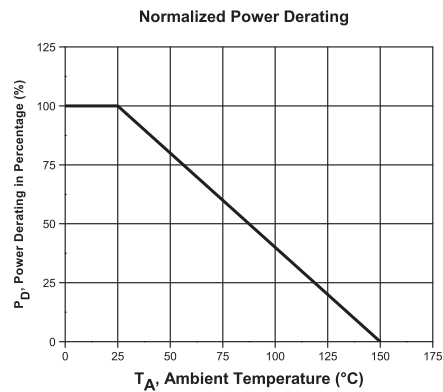
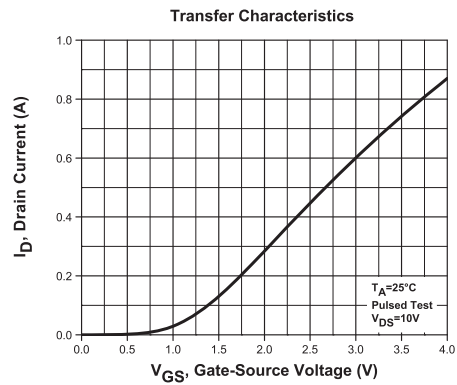
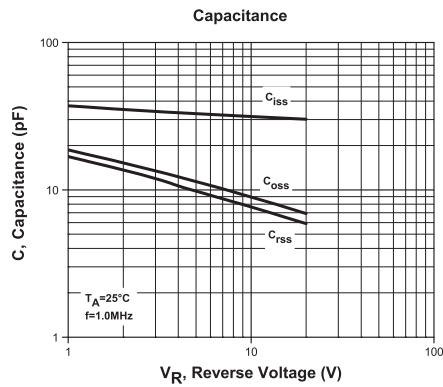
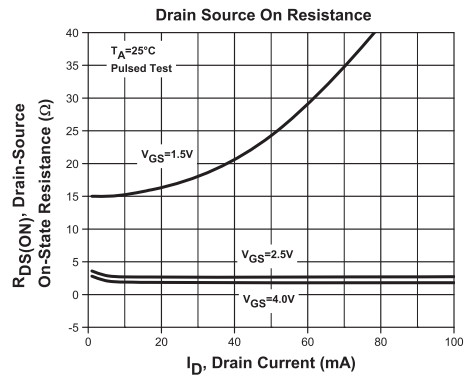
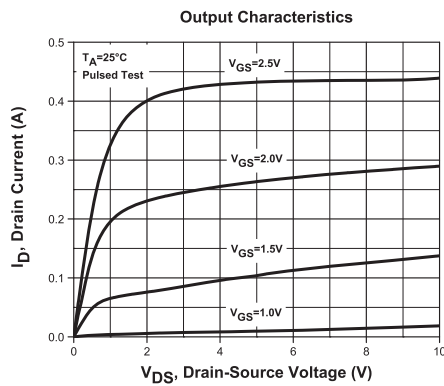
PRINCIPAL DEVICE TYPES

CEDM8001
CMNDM8001

R1 (2-September 2010)

PROCESS CP761R

Typical Electrical Characteristics



R1 (2-September 2010)